



**THE DATASHEET OF
DMG4932LSD-13**



ASYMETRICAL DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

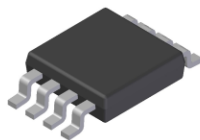
Features

- High Density UMOS with Schottky Barrier Diode
- Low Leakage Current at High Temp.
- High Conversion Efficiency
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Utilizes Diodes Incorporated's Monolithic DIOFET Technology to Increase Conversion Efficiency
- 100% UIS and R_g Tested
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

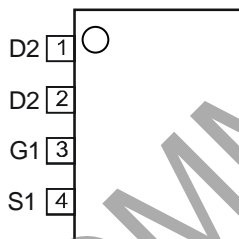
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.072 grams (Approximate)

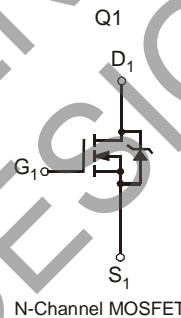
DIOFET
Schottky Integrated MOSFET



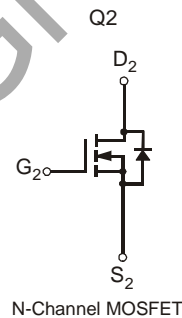
Top View



Top View
Internal Schematic



N-Channel MOSFET



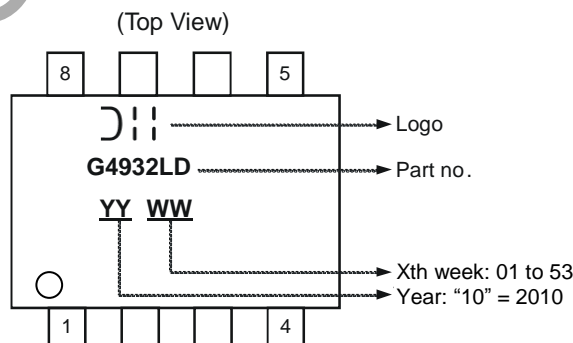
N-Channel MOSFET

Ordering Information (Note 4)

Part Number	Case	Packaging
DMG4932LSD-13	SO-8	2500 / Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



Maximum Ratings – Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 5)	Steady State	T _A = +25°C	I _D	9.5	A
		T _A = +85°C		7.2	
Pulsed Drain Current (Note 6)			I _{DM}	40	A
Avalanche Current (Notes 6 & 7)			I _{AR}	13	A
Repetitive Avalanche Energy (Notes 6 & 7) L = 0.3mH			E _{AR}	25.4	mJ

Maximum Ratings – Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 5)	Steady State	T _A = +25°C	I _D	9.5	A
		T _A = +85°C		7.5	
Pulsed Drain Current (Note 6)			I _{DM}	40	A
Avalanche Current (Notes 6 & 7)			I _{AR}	13	A
Repetitive Avalanche Energy (Notes 6 & 7) L = 0.3mH			E _{AR}	25.4	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	1.19	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	R _{θJA}	107	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Notes:
5. Device mounted on FR-4 PCB with minimum recommended pad layout. The value in any given application depends on the user's specific board design.
 6. Repetitive rating, pulse width limited by junction temperature.
 7. I_{AR} and E_{AR} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

Electrical Characteristics – Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	0.1	mA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	—	2.4	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	10	15	mΩ	V _{GS} = 10V, I _D = 9A
			12	18		V _{GS} = 4.5V, I _D = 7A
Forward Transfer Admittance	Y _{fs}	—	14	—	S	V _{DS} = 10V, I _D = 9A
Diode Forward Voltage	V _{SD}	—	0.4	0.6	V	V _{GS} = 0V, I _S = 1A
Maximum Body-Diode + Schottky Continuous Current	I _S	—	—	5	A	—
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	1932	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	154	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	121	—	pF	
Gate Resistance	R _g	—	2.68	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (4.5V)	Q _g	—	18.1	—	nC	V _{DS} = 15V, V _{GS} = 10V, I _D = 9A
Total Gate Charge (10V)	Q _g	—	42.0	—	nC	
Gate-Source Charge	Q _{gs}	—	4.5	—	nC	
Gate-Drain Charge	Q _{gd}	—	4.0	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	6.16	—	ns	
Turn-On Rise Time	t _R	—	7.22	—	ns	V _{GS} = 10V, V _{DS} = 15V, R _G = 3Ω, R _L = 1.7Ω
Turn-Off Delay Time	t _{D(OFF)}	—	36.76	—	ns	
Turn-Off Fall Time	t _F	—	5.38	—	ns	

- Notes:
8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to production testing.

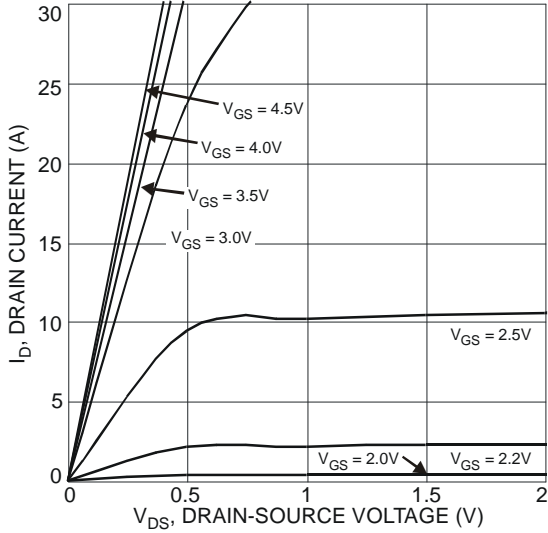


Fig. 1 Typical Output Characteristic

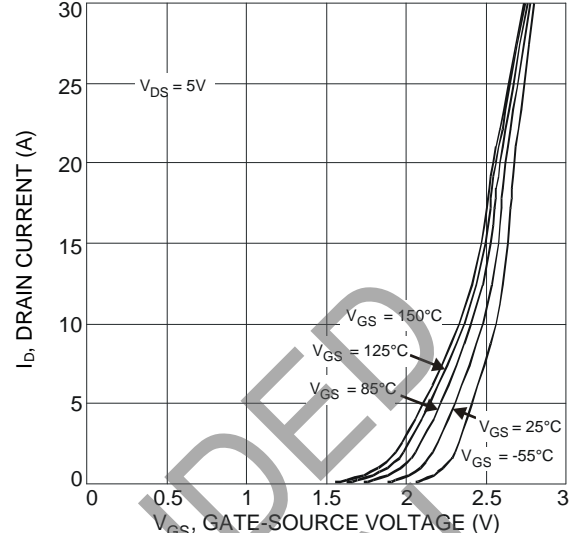


Fig. 2 Typical Transfer Characteristic

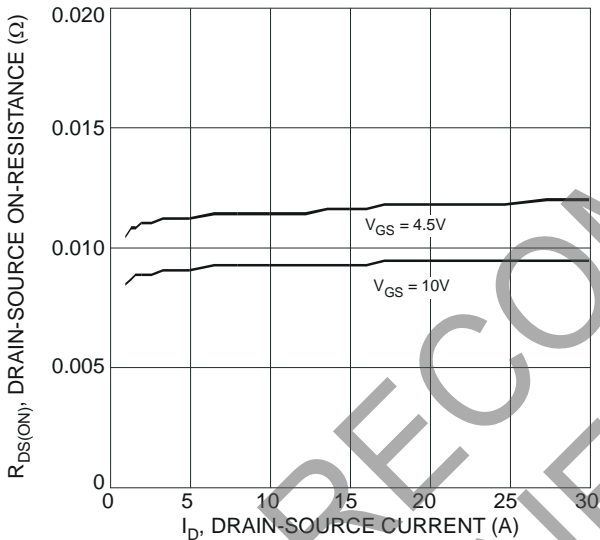


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

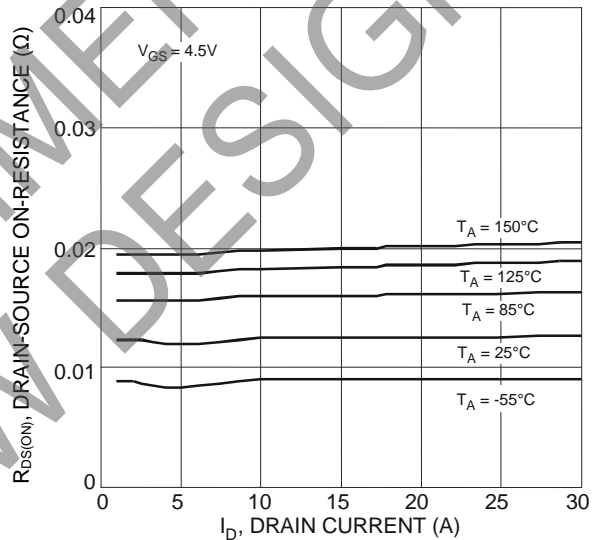


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

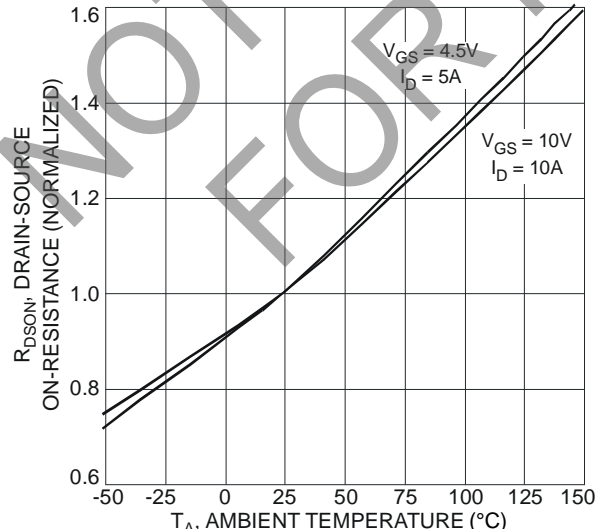


Fig. 5 On-Resistance Variation with Temperature

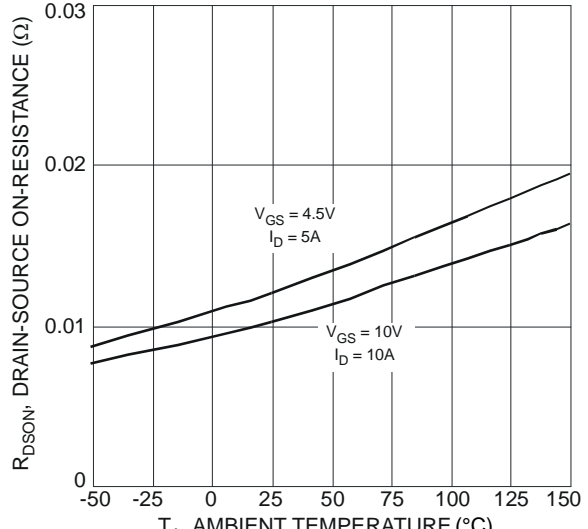


Fig. 6 On-Resistance Variation with Temperature

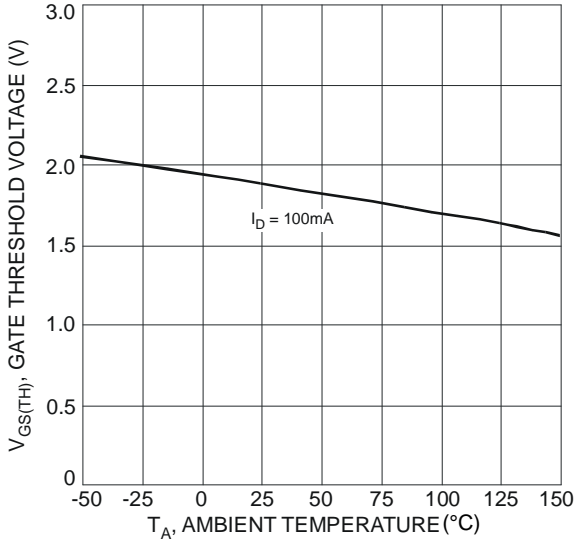


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

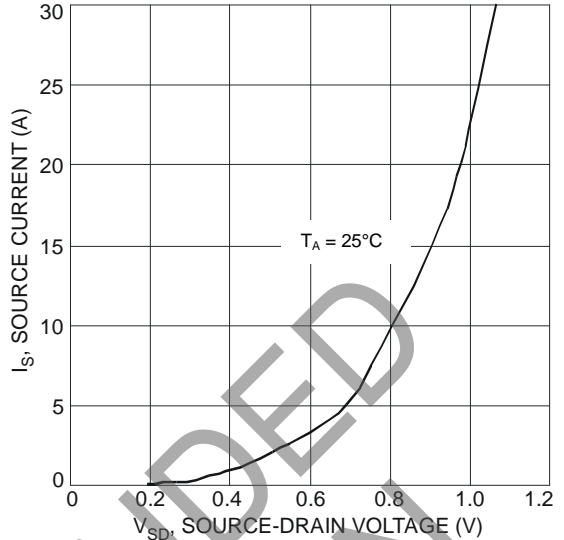


Fig. 8 Diode Forward Voltage vs. Current

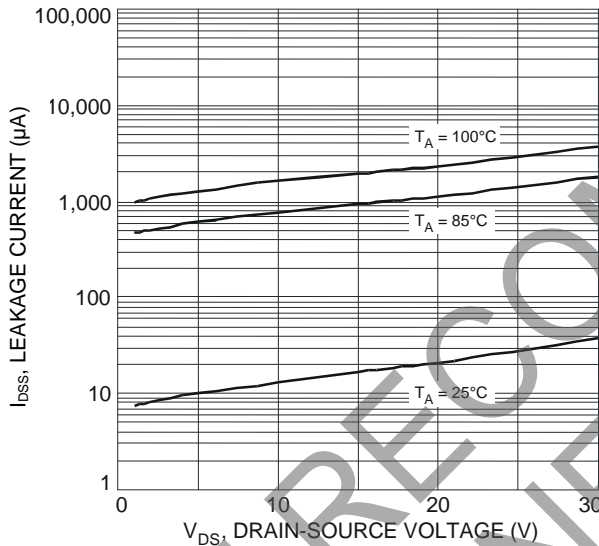


Fig. 9 Typical Leakage Current vs. Drain-Source Voltage

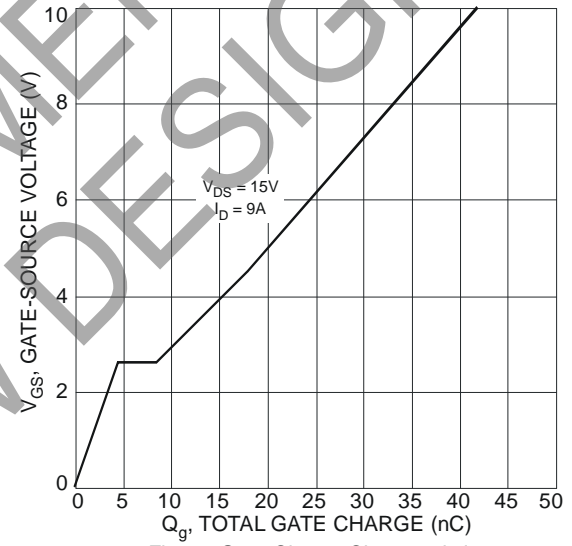


Fig. 10 Gate-Charge Characteristics

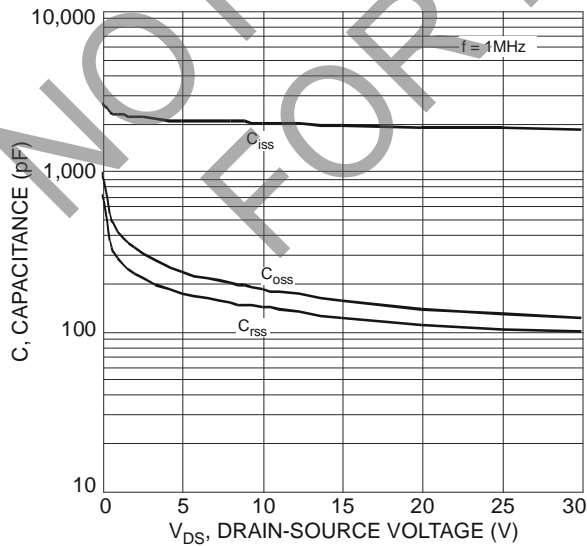
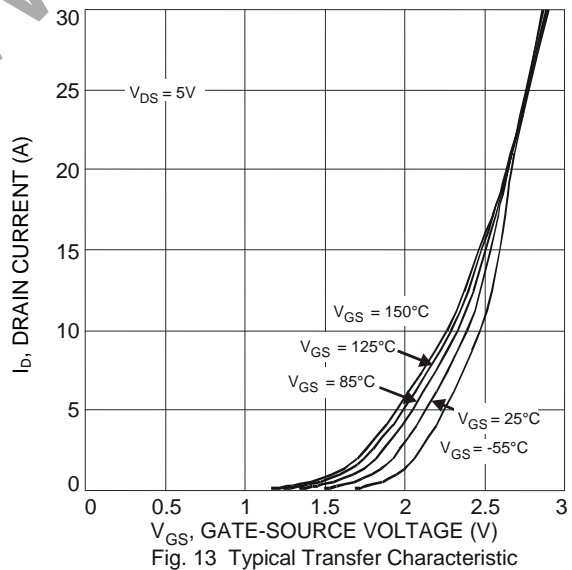
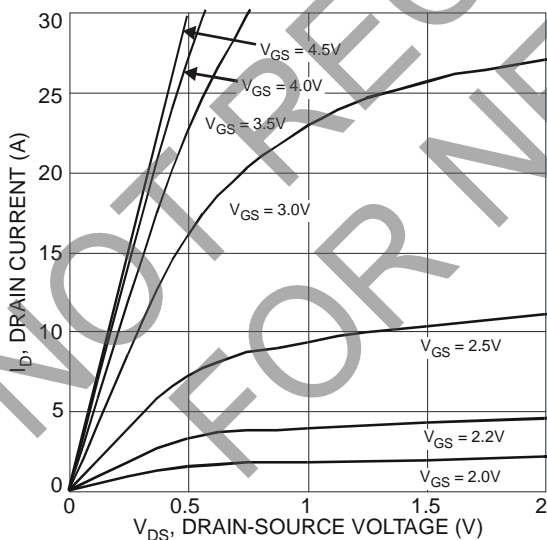


Fig. 11 Typical Total Capacitance

Electrical Characteristics – Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	+100	nA	V _{GS} = +25V, V _{DS} = 0V
		—	—	-800		V _{GS} = -25V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	—	2.3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	12	15.8	mΩ	V _{GS} = 10V, I _D = 9A
		—	16	23		V _{GS} = 4.5V, I _D = 7A
Forward Transfer Admittance	Y _{fs}	—	8	—	S	V _{DS} = 10V, I _D = 9A
Diode Forward Voltage	V _{SD}	—	0.65	1.0	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	675	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	98	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	90	—	pF	
Gate Resistance	R _g	—	1.6	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (4.5V)	Q _g	—	7.8	—	nC	V _{DS} = 15V, V _{GS} = 10V, I _D = 9A
Total Gate Charge (10V)	Q _g	—	16.0	—	nC	
Gate-Source Charge	Q _{gs}	—	1.9	—	nC	
Gate-Drain Charge	Q _{gd}	—	2.6	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	5.05	—	ns	
Turn-On Rise Time	t _R	—	9.21	—	ns	V _{GS} = 10V, V _{DS} = 15V, R _G = 3Ω, R _L = 1.7Ω
Turn-Off Delay Time	t _{D(OFF)}	—	20.76	—	ns	
Turn-Off Fall Time	t _F	—	4.94	—	ns	

Notes: 8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to production testing.



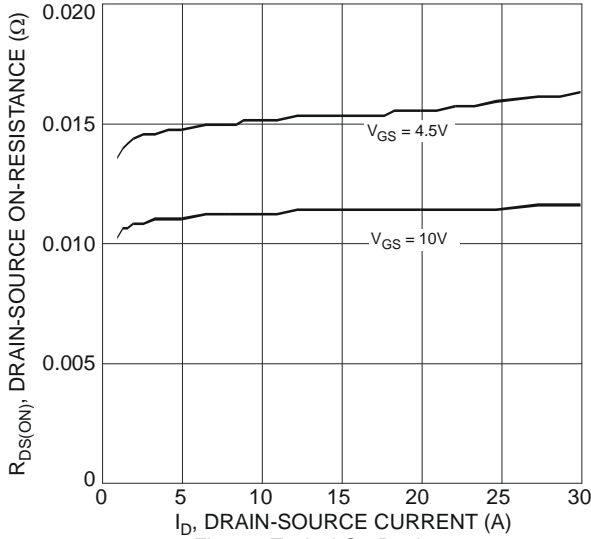


Fig. 14 Typical On-Resistance vs. Drain Current and Gate Voltage

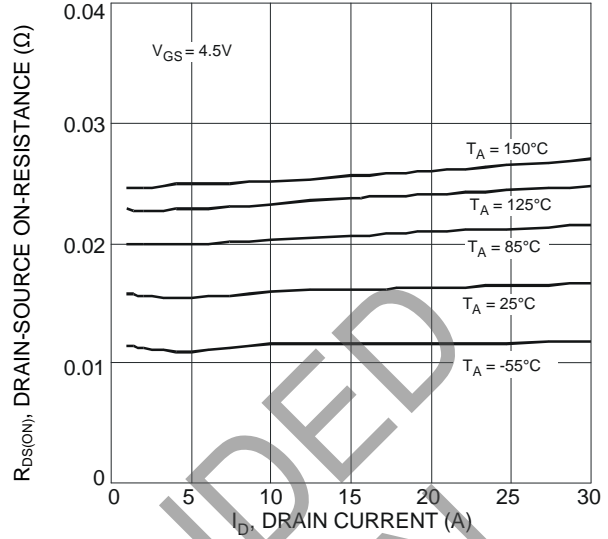


Fig. 15 Typical On-Resistance vs. Drain Current and Temperature

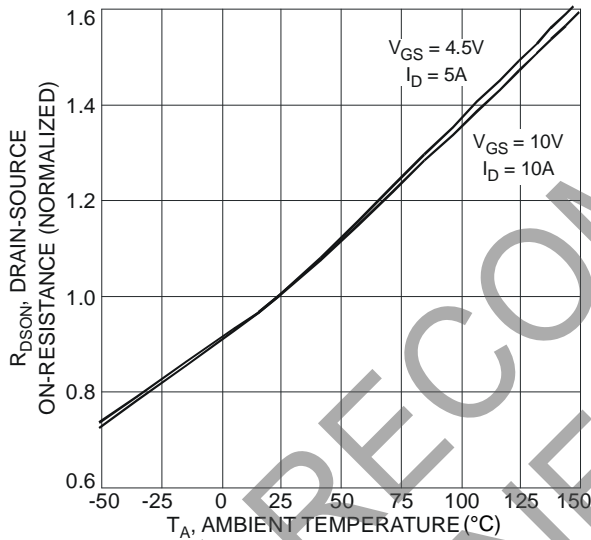


Fig. 16 On-Resistance Variation with Temperature

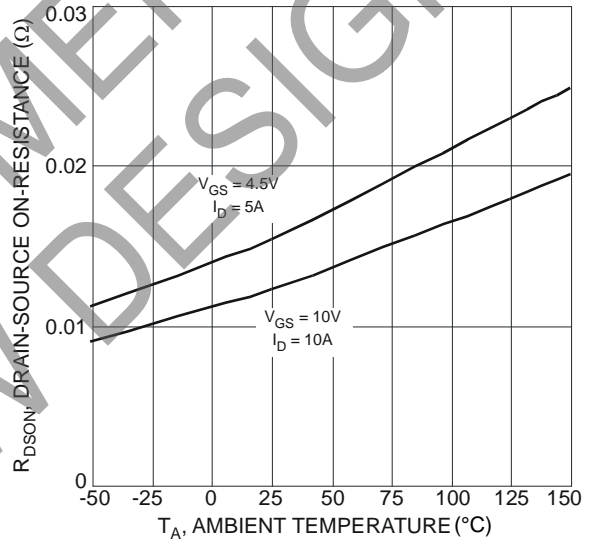


Fig. 17 On-Resistance Variation with Temperature

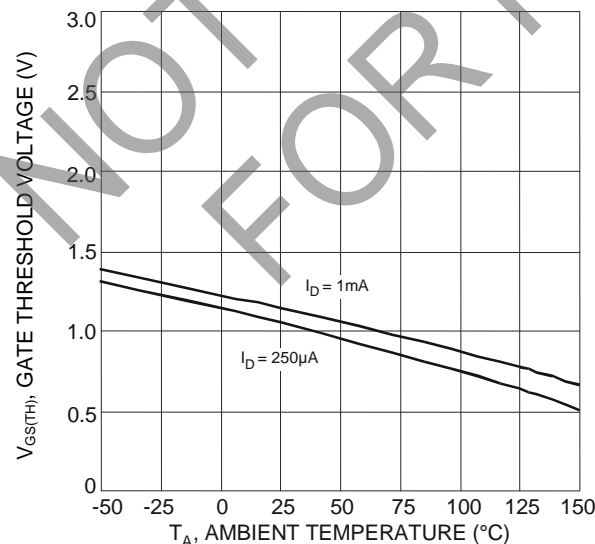


Fig. 18 Gate Threshold Variation vs. Ambient Temperature

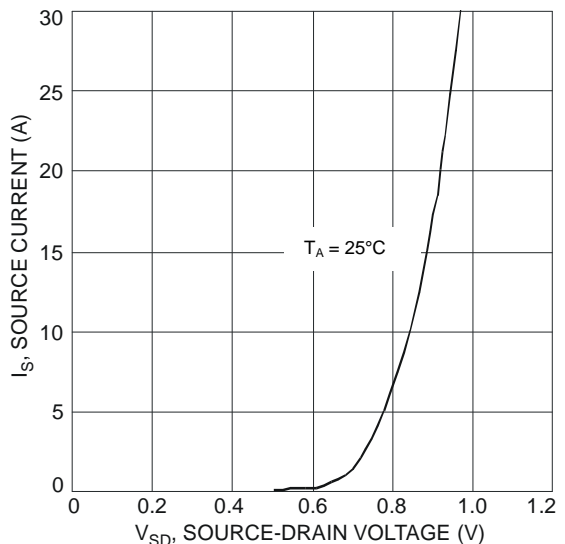


Fig. 19 Diode Forward Voltage vs. Current

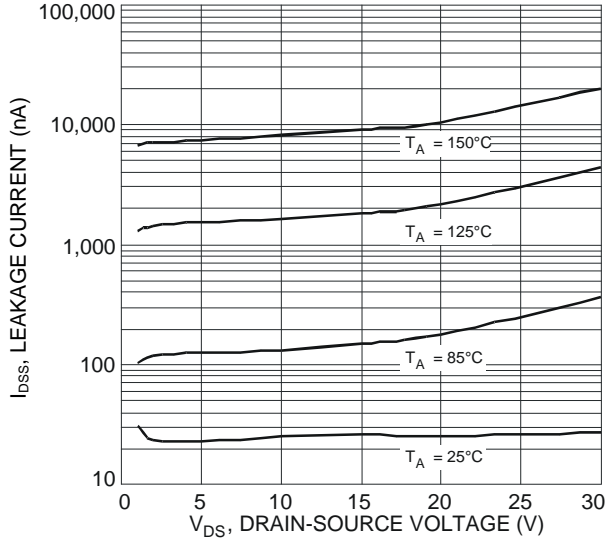


Fig. 20 Typical Leakage Current vs. Drain-Source Voltage

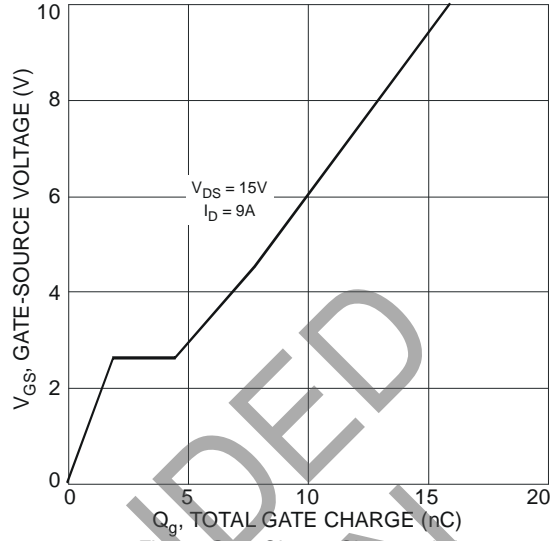


Fig. 21 Gate-Charge Characteristics

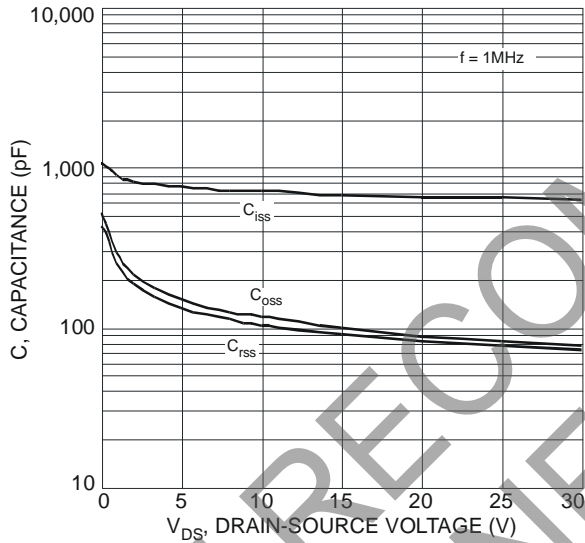


Fig. 22 Typical Total Capacitance

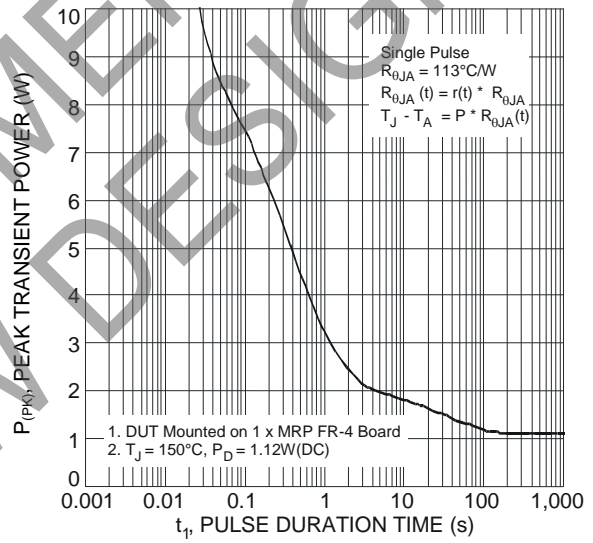


Fig. 23 Single Pulse Maximum Power Dissipation

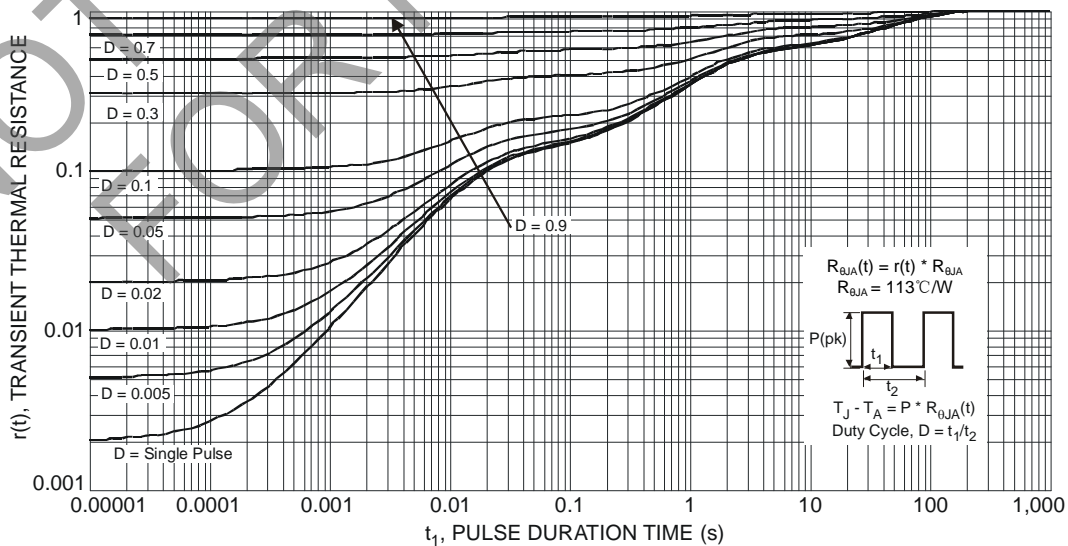
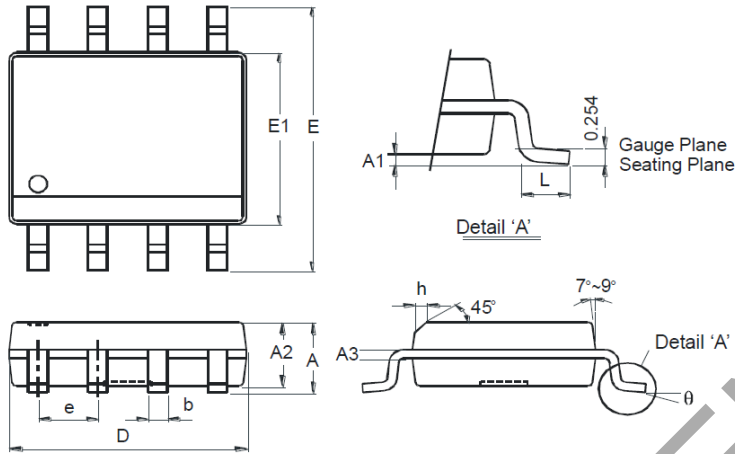


Fig. 24 Transient Thermal Response

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8

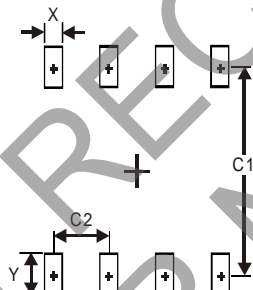


SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h		0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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